

TECHNICAL DATA
DATASHEET 5309, Rev A

Diode Array

- **Devices Are Serialized**
- **Built And Screened To Space Level Quality**
- **Space Quality Level Conformance Testing Is Performed On Each Lot**

MAX. RATINGS / ELECTRICAL CHARACTERISTICS FOR EACH DIODE

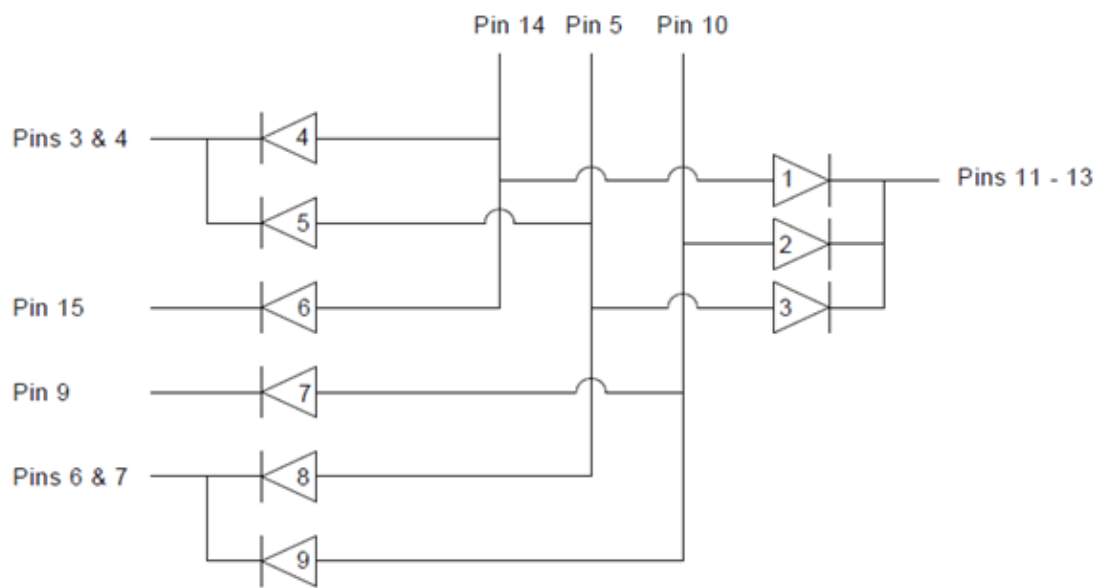
All rating at are $T_A = 25^{\circ}\text{C}$ unless otherwise specified

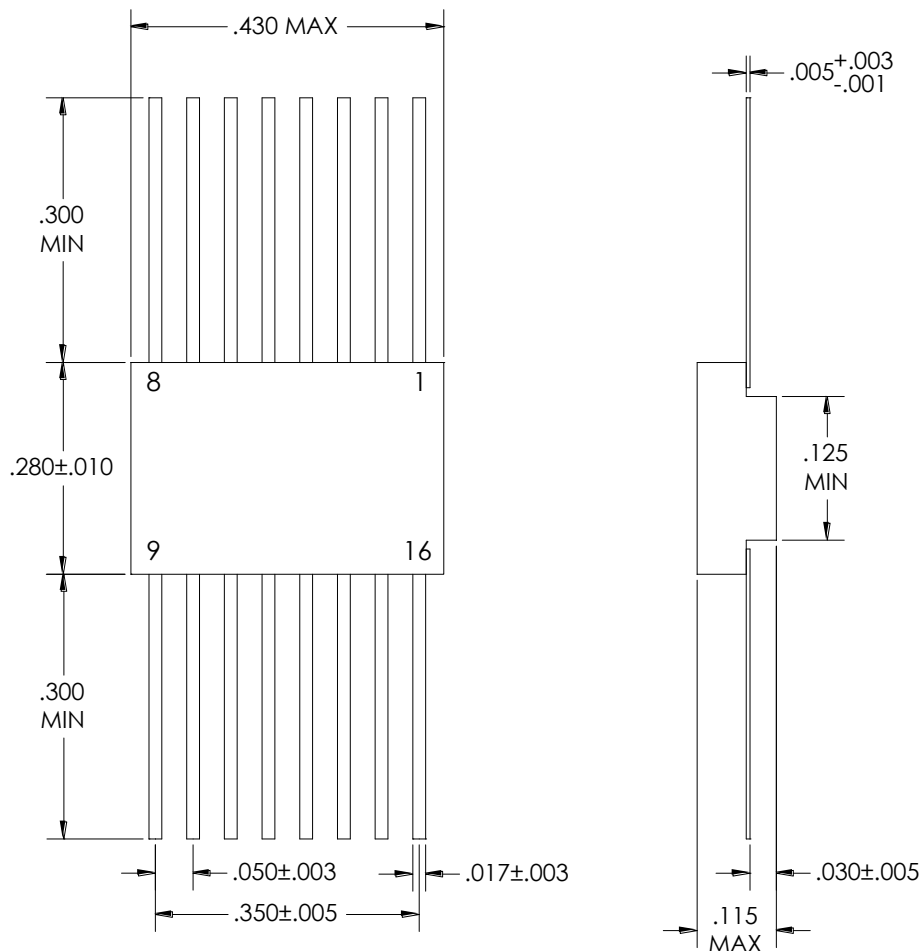
RATING	SYMBOL	MAX	UNIT
Peak Inverse Voltage (DC)	PIV	75	V
Average DC Output Current Per diode	I_O	50	mA
Peak Single Cycle Surge Current ^{(1) (2)} ($T_P=8.3\text{ms}$ single half-Sine wave)	I_{FSM}	500	mA
Peak Repetitive Surge Current ^{(1) (3)} ($T_P=8.3\text{ms}$ half-Sine wave)	I_{FRM}	300	mA
Steady State Power Dissipation per Diode Junction	P_D	400	mW
Steady State Power Dissipation per Package ⁽³⁾	P_T	500	mW
Max. Operating Junction Temperature	T_J	-65 to +150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +200	$^{\circ}\text{C}$
Max. Forward Voltage $I_F = 10\text{mA}$	V_{F1}	1	V
Max. Forward Voltage Match $I_F = 10\text{mA}$	V_{FM}	5	mV
Max. Reverse Current $V_R = 20\text{V}$ $V_R = 40\text{V}$	I_{R1} I_{R2}	50 100	nA
Max. Reverse Recovery Time $I_F = 10\text{mA}$, $I_{RM} = 10\text{mA}$	t_{RR}	10	ns
Max. Capacitance $f = 1\text{MHz}$, $V_R = 0\text{V}$	C_T	5	pF

Note: (1) Each diode
(2) Derate at $2.4\text{mA}/^{\circ}\text{C}$ above 25°C
(3) Derate at $4.0\text{mA}/^{\circ}\text{C}$ above 25°C

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Electrical Schematic



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